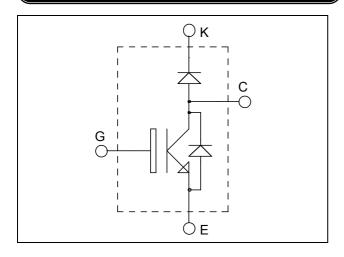


# APT40GL120JU2

# ISOTOP<sup>®</sup> Boost chopper Trench + Field Stop IGBT4 Power module





# $V_{CES} = 1200V$ $I_C = 40A$ @ Tc = 80°C

### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

#### Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

### Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
I <sub>C</sub>	Continuous Collector Current	$T_C = 25^{\circ}C$	65	
$\mathbf{I}_{\mathrm{C}}$	Continuous Conector Current	$T_C = 80^{\circ}C$	40	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	70	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	220	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	70A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics							
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.25	V
		$I_{\rm C} = 35 {\rm A}$ $T_{\rm j} = 150^{\circ} {\rm C}$		2.25		v	
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.2 \text{mA}$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

## **Dynamic Characteristics**

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Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			1950		
Coes	Output Capacitance				155		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz			115		
Q <sub>G</sub>	Gate charge	$V_{GE} = \pm 15V$ ; $V_{CE} = 600V$ $I_{C} = 35A$			0.27		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switc	hing (25°C)		130		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			20		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{CE} = 600V$ $I_C = 35A$ $R_G = 12\Omega$			300		ns
T <sub>f</sub>	Fall Time				45		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 35A$			150		ns
T <sub>r</sub>	Rise Time				35		
T <sub>d(off)</sub>	Turn-off Delay Time				350		
T <sub>f</sub>	Fall Time	$R_G = 12\Omega$			80		
Eon	Turn on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		2.6		mJ
Lon	Turn-on Switching Energy	$V_{CE} = 600V$	$T_{\rm J} = 150^{\circ}{\rm C}$		4		1115
E <sub>off</sub>	Turn-off Switching Energy	$I_C = 35A$	$T_J = 25^{\circ}C$		2		mJ
Loff	Turn-on Ownening Litergy	$R_G = 12\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		3		1115
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10\mu s$ ; $T_j = 150^{\circ}C$			140		А

### Chopper diode ratings and characteristics

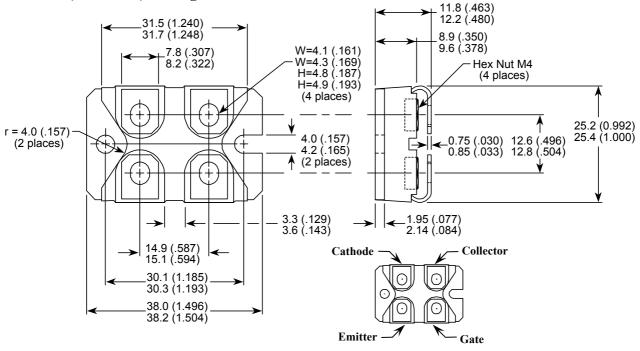
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1200			V
I	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			100	
I <sub>RM</sub>			$T_{j} = 150^{\circ}C$			500	μA
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		30		А
	Diode Forward Voltage	$I_F = 30A$			2.6	3.1	
$V_{\rm F}$		$I_F = 60A$			3.2		V
		$I_F = 30A$	$T_{i} = 125^{\circ}C$		1.8		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		300		ns
ι <sub>rr</sub>	Reverse Recovery Time	$I_{\rm F} = 30A$ $V_{\rm R} = 800V$	$T_{j} = 125^{\circ}C$		380		115
Q <sub>rr</sub>	Reverse Recovery Charge	$di/dt = 200 A/\mu s$ $T_j = 25^{\circ}C$	$T_j = 25^{\circ}C$		360		nC
Qrr	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		1700		ne



## Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance IGBT Diode	IGBT			0.68	°C/W	
		Diode			1.2		
R <sub>thJA</sub>	Junction to Ambient (IGBT & Diode)				20		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		2500			V	
$T_J, T_{STG}$	Storage Temperature Range		-55		175	°C	
$T_{\rm L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	C	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m	
Wt	Package Weight			29.2		g	

### SOT-227 (ISOTOP<sup>®</sup>) Package Outline

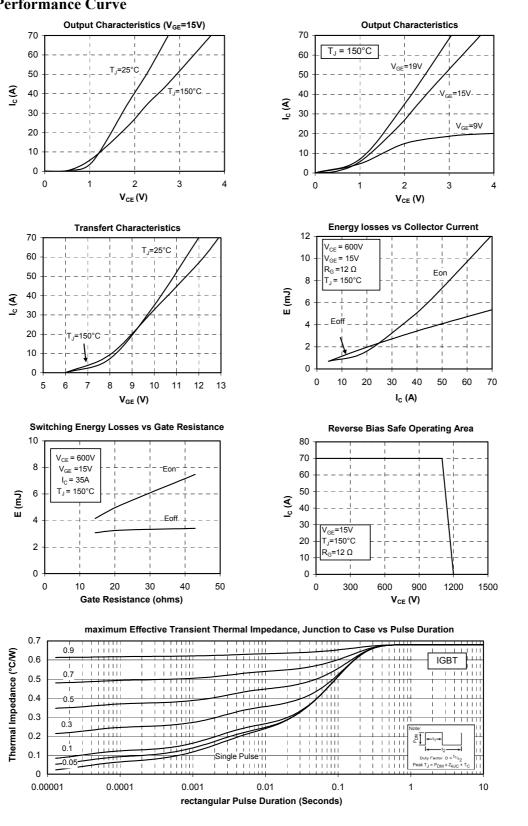


Dimensions in Millimeters and (Inches)

ISOTOP® is a registered trademark of ST Microelectronics NV



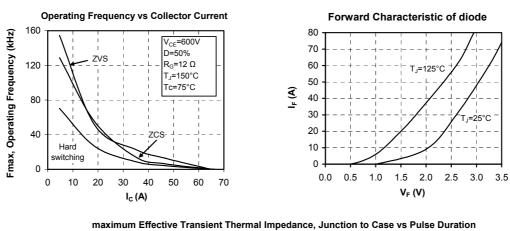
#### **Typical Performance Curve**

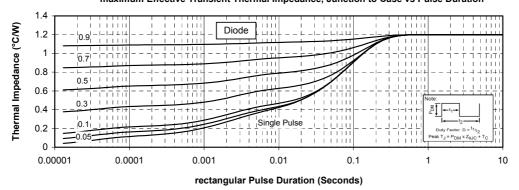


APT40GL120JU2 - Rev 1 October, 2012



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